

IN THE SPECIFICATION

Please amend the paragraph at page 2, lines 8-20, as follows:

If a depo-process is followed by a depoless-process in a same chamber while dry etching a silicon oxide film, an etching rate of the depoless-process becomes unstable, since the depoless-process can be easily influenced by deposits produced in the same chamber during the preceding depo-process. The term "depo-process" used herein denotes a process of using a gas with a smaller F/C (~~fluorine/chlorine~~) (fluorine/carbon) ratio, e.g., C₄F₈, which leaves a visible amount of polymers including a CF based element such as CF₄ attached to the chamber. The term "depoless-process" used herein denotes a process using a gas with a larger F/C ratio, e.g., CF₄, which leaves no polymers attached to the chamber.